Supporting Information

Flux Induced Crystal Phase Transition in Vapor-Liquid-Solid Growth of Indium-Tin Oxide Nanowires

Gang Meng,^{*a*} Takeshi Yanagida,^{**a*} Hideto Yoshida,^{*a*} Kazuki Nagashima,^{*a*} Masaki Kanai,^{*a*} Fuwei Zhuge,^{*a*} Yong He,^{*a*} Annop Klamchuen,^{*a*} Sakon Rahong,^{*a*} Xiaodong Fang,^{*b*} Seiji Takeda^{*a*} and Tomoji Kawai^{*a*}

^a The Institute of Scientific and Industrial Research, Osaka University, 8-1 Mihogaoka Ibaraki, Osaka, 567-0047, Japan

^b Anhui Institute of Optics and Fine Mechanics, Chinese Academy of Sciences, Hefei 230031, China



Fig. S1 Typical STEM mapping data of ISO nanowires.



Fig. S2 Homogeneity of ISO phase along the entire length of nanowire. HRTEM images of ISO nanowires taken from tip (area A), middle (area B) and root (area C) have been examined. The insets show the corresponding fast Fourier transform (FFT) images.